

In The Specification

Paragraph 0017 has been amended as follows:

0017 In the wafer blade for picking up or delivering wafers, the strain sensor may be a piezoelectric sensing device, or may be a sensor that is sensitive to at least $1\text{ }\mu\text{m}$ ~~strain~~ displacement. The blade body may be formed in the shape of a fork, or may be formed in the shape of a rectangle. The blade body may be formed of metal or ceramic. The strain sensor may be provided in the shape of a thin film.

Paragraph 0036 has been amended as follows:

0036 The strain sensor utilized by the present invention can be any type of sensor that is provided in a thin film configuration. The strain sensor should be sensitive to very small ~~strains~~ displacement, such as ~~strains~~ displacement as small as $1\text{ }\mu\text{m}$. One of such suitable strain sensors to be utilized by the present invention wafer blade may be a piezoelectric thin film sensor. When the piezoelectric thin film sensor makes a

mechanical contact with a surface, an electric field is produced and a signal in the form of an electrical current can be amplified and sent to an alarm panel.

Paragraph 0039 has been amended as follows:

0039 The sensitivity of the piezoelectric thin film sensor 70 must be such that any minute mechanical contact with a wafer below the wafer blade during operation can be detected. For instance, a ~~strain~~ displacement caused by the contact force as small as 1 μm should be detected and an electric field amplified to produce an electrical signal for the alarm panel 80 shown in Figure 4.